

Simulazioni



Monte Carlo Simulations and Measurements with the Accelerator of the department



and double-strand breaks of the DNA.

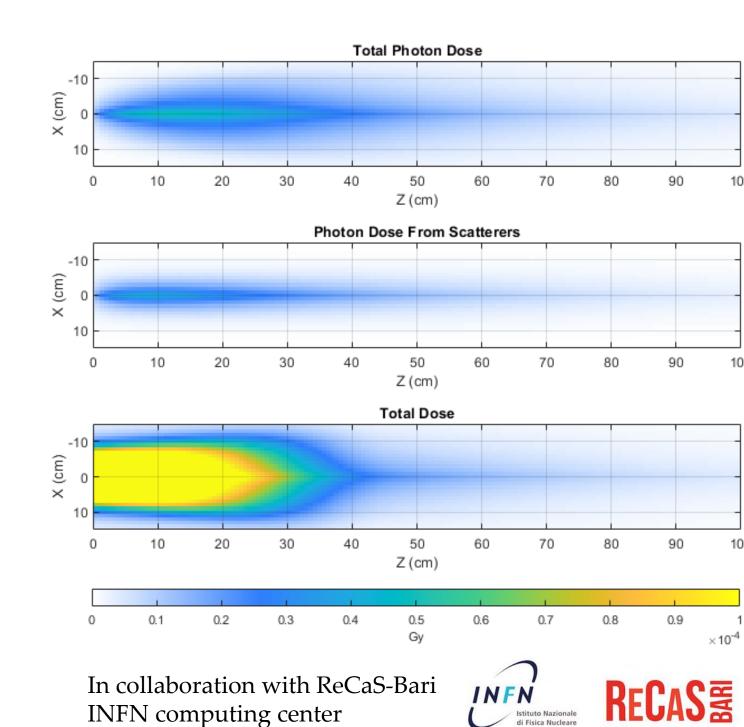
In particle physics, Monte Carlo algorithms are primarily used to estimate physical quantities during particle interactions. It is a standard approach for radioprotection studies used to estimate the energy deposition in different materials.







TOPAS MC wraps and extends the Geant4 libraries and has been designed for medical physics applications to produce fast results by a broad spectrum of users, from clinicians to researchers. It is the primary tool used by researchers in medical accelerator facilities. Similarly, AllPix Squared toolkit can be used to track the deposited charges inside silicon sensors by taking into account charge carriers mobility and diffusion models



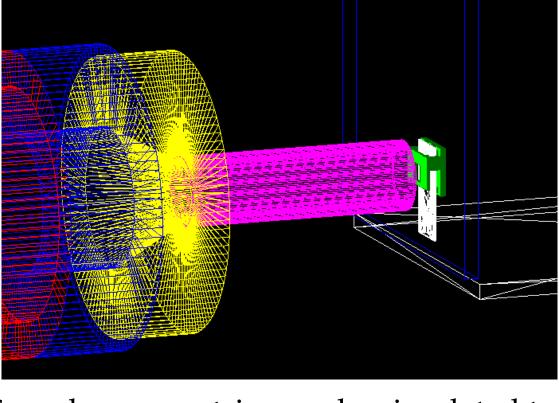
Comparison of dose profiles for electrons of 10 MeV

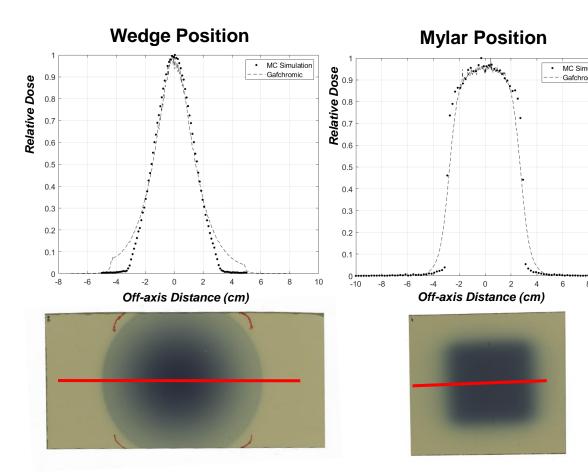
Geant4 libraries are based on validated data of particle cross-

molecular level these algorithms can quantify radicals or single

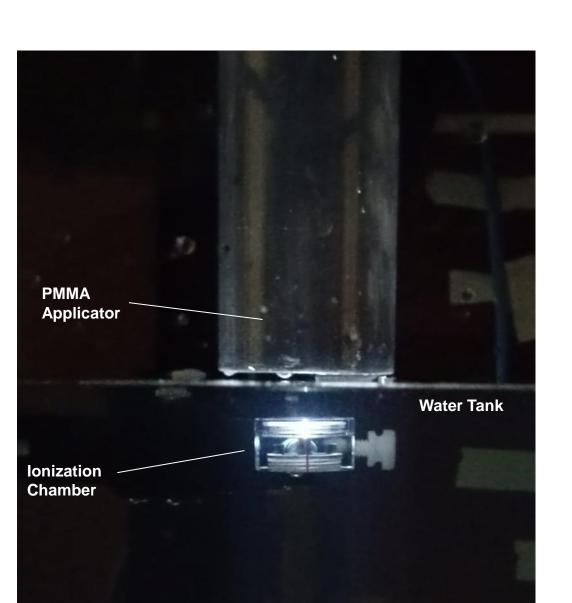
sections for a wide range of energies and allow to study the

biological damage on both macro and micro scales. At the

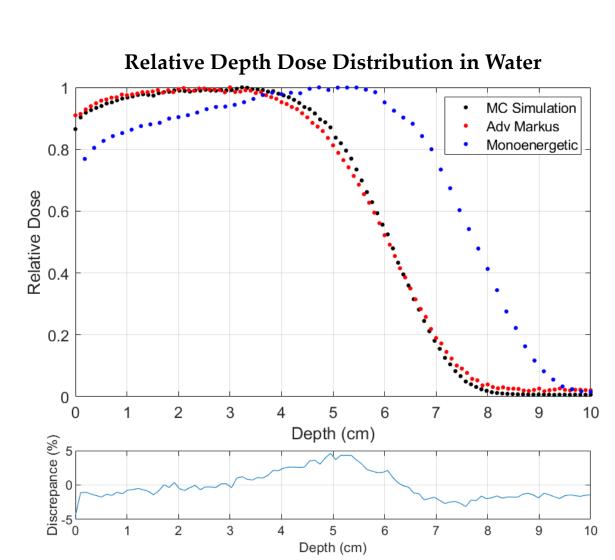


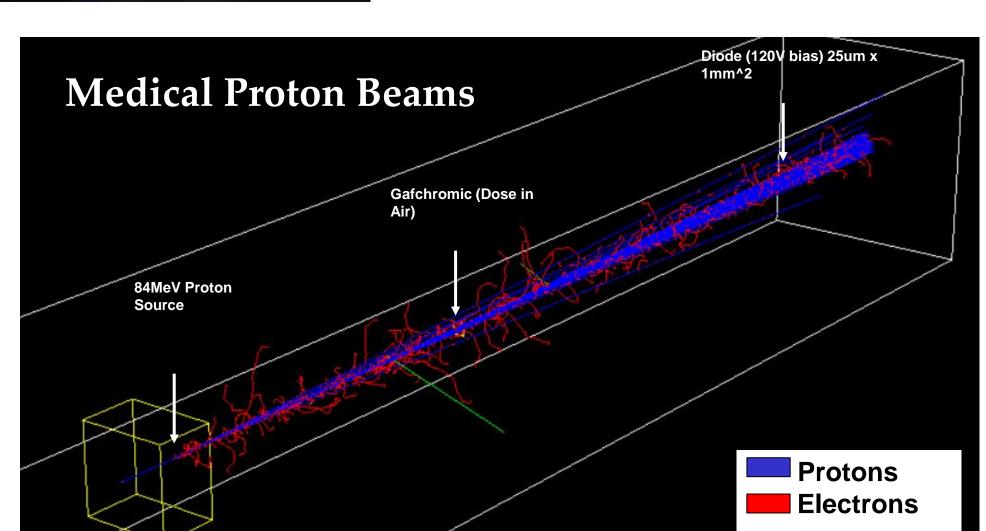


Complex geometries can be simulated to quantify the contribution to the dose of different objects in an experimental setup

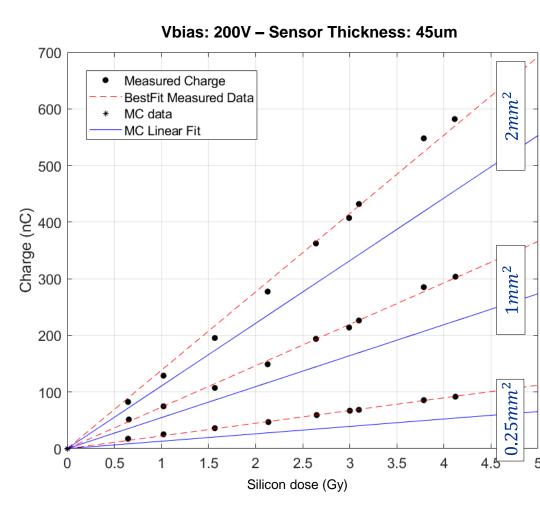


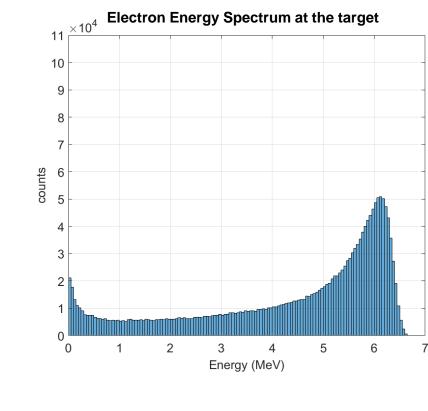
Sentaurus





Simulated Deposited Charge in Silicon Sensor

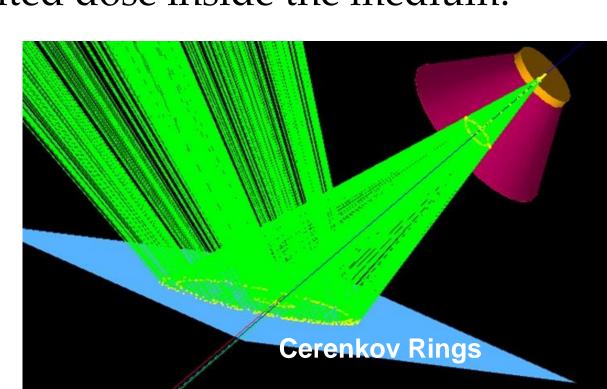


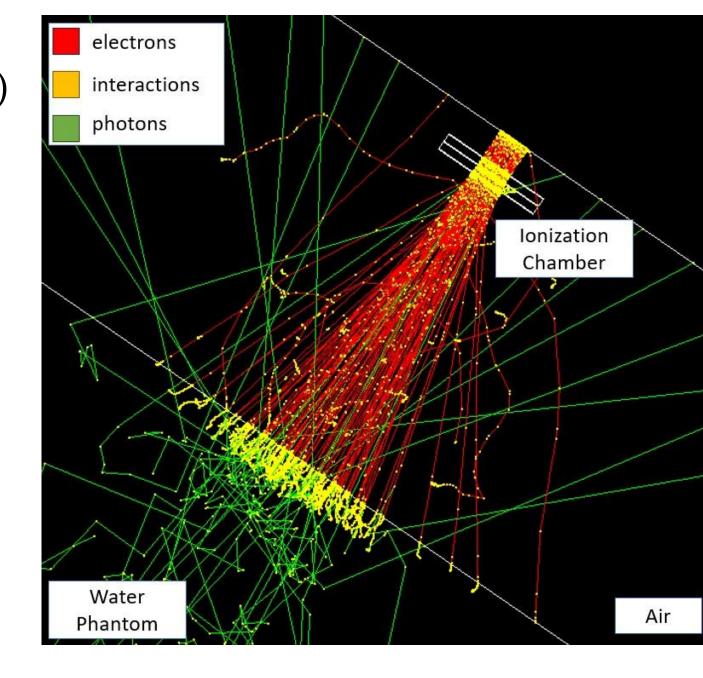




Cerenkov radiation simulations with optical photons and **Ionization Chamber**

Cerenkov radiation is a promising candidate for Ultra-High Dose Rates Dosimetry (FLASH) because the energy loss has a very weak dependence on the energy, therefore the light intensity should be proportional to the deposited dose inside the medium.





TCAD Geometry, doping, mesh definitions SYNOPSYS mesh refinement I-V characterization Space Charge Doping concentration I-V characterization Reverse Bias ConductionBandEnergy DopingConcentration

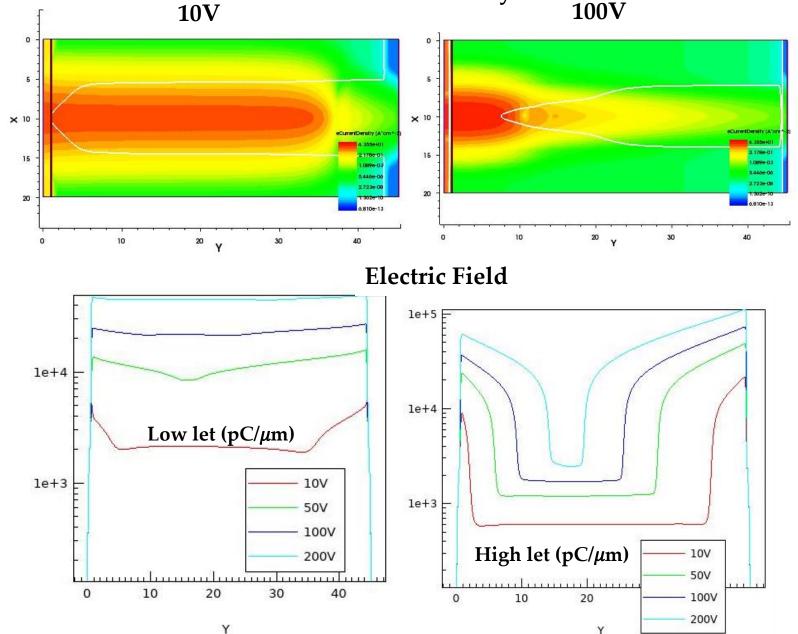
Sensor thickness (μ m)

Sensor thickness (μ m)

Charge carriers distributions in semiconductors

TCAD Sentaurus Synopsys

Optical generation Gamma radiation Alpha particles Heavy Ions eCurrentDensity 100V10V



Output signals study

Signal generated on the electrods from carriers (electrons and holes)

